

HT11G - HT18G

1.0 AMP. Glass Passivated High Efficient Rectifiers

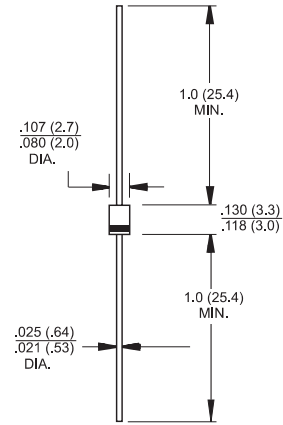
TS-1

Features

- ✧ Glass passivated chip junction.
- ✧ High efficiency, Low VF
- ✧ High current capability
- ✧ High reliability
- ✧ High surge current capability
- ✧ For use in low voltage, high frequency inverter, free wheeling, and polarity protection application.

Mechanical Data

- ✧ Case: Molded plastic TS-1
- ✧ Epoxy: UL 94V0 rate flame retardant
- ✧ Lead: Pure tin plated, lead free, solderable per MIL-STD-202, Method 208 guaranteed
- ✧ Polarity: Color band denotes cathode
- ✧ High temperature soldering guaranteed: 260°C/10 seconds/.375", (9.5mm) lead lengths at 5 lbs., (2.3kg) tension
- ✧ Mounting position: Any
- ✧ Weight: 0.20 gram



Dimensions in inches and (millimeters)

Maximum Ratings and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified.
 Single phase, half wave, 60 Hz, resistive or inductive load.
 For capacitive load, derate current by 20%

Type Number	Symbol	HT 11G	HT 12G	HT 13G	HT 14G	HT 15G	HT 16G	HT 17G	HT 18G	Units	
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	300	400	600	800	1000	V	
Maximum RMS Voltage	V_{RMS}	35	70	140	210	280	420	560	700	V	
Maximum DC Blocking Voltage	V_{DC}	50	100	200	300	400	600	800	1000	V	
Maximum Average Forward Rectified Current .375 (9.5mm) Lead Length @ $T_A = 55^\circ C$	$I_{(AV)}$	1.0								A	
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	30								A	
Maximum Instantaneous Forward Voltage @ 1.0A	V_F	1.0			1.3		1.7			V	
Maximum DC Reverse Current @ $T_A=25^\circ C$ at Rated DC Blocking Voltage @ $T_A=125^\circ C$	I_R	5.0					150				μA μA
Maximum Reverse Recovery Time (Note 1)	T_{rr}	50				75				nS	
Typical Junction Capacitance (Note 2)	C_j	15				10				pF	
Typical Thermal Resistance	$R_{\theta JA}$	95								$^\circ C/W$	
Operating Temperature Range	T_J	-65 to +150								$^\circ C$	
Storage Temperature Range	T_{STG}	-65 to +150								$^\circ C$	

- Notes:
1. Reverse Recovery Test Conditions: $I_F=0.5A$, $I_R=1.0A$, $I_{RR}=0.25A$
 2. Measured at 1 MHz and Applied Reverse Voltage of 4.0 V D.C.
 3. Mount on cu-Pad Size 5mm x 5mm on PCB.

RATINGS AND CHARACTERISTIC CURVES (HT11G THRU HT18G)

FIG.1- MAXIMUM FORWARD CURRENT DERATING CURVE

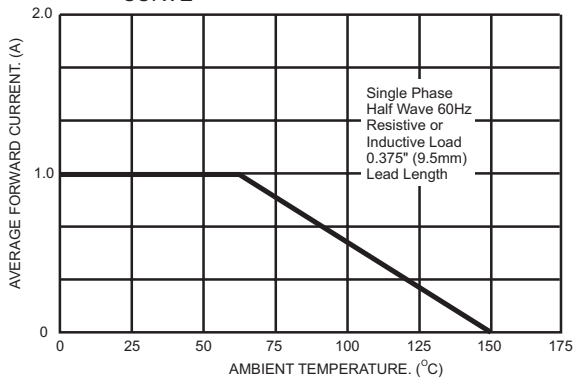


FIG.2- TYPICAL REVERSE CHARACTERISTICS

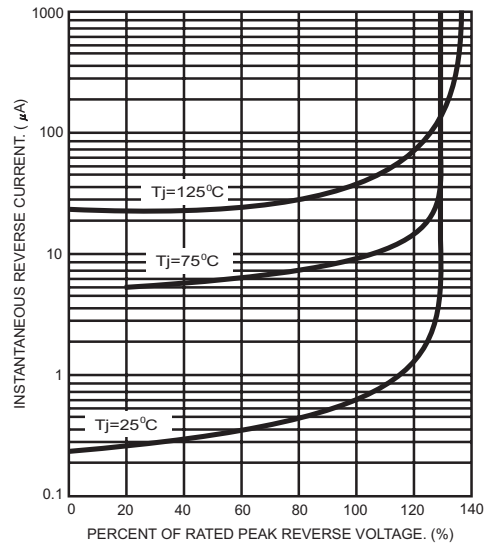


FIG.3- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

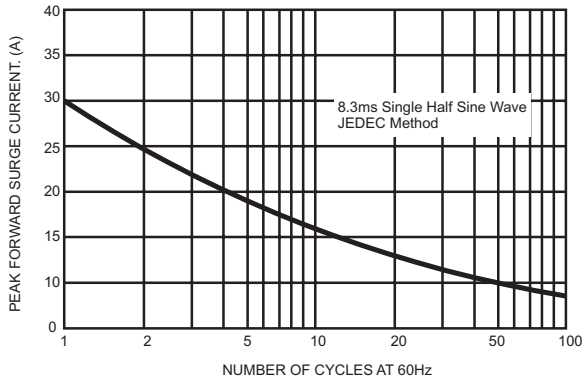


FIG.5- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

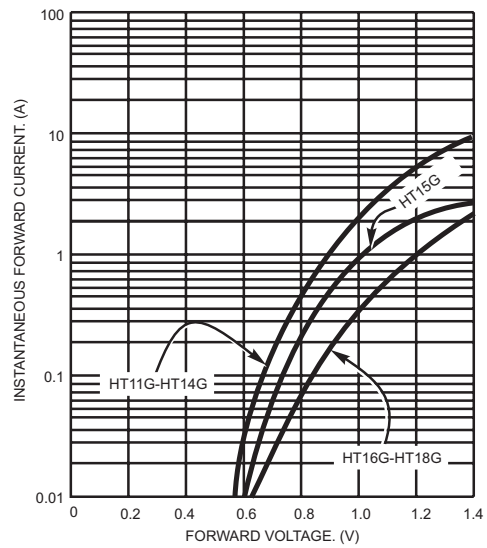


FIG.4- TYPICAL JUNCTION CAPACITANCE

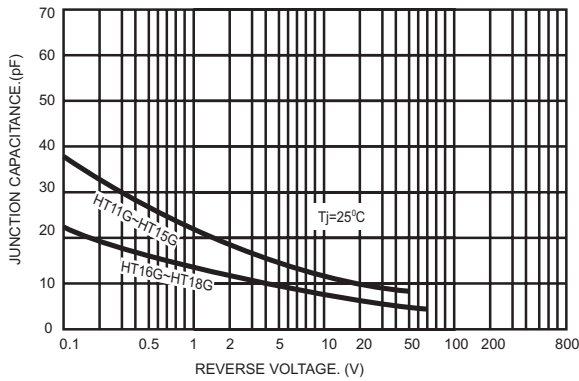
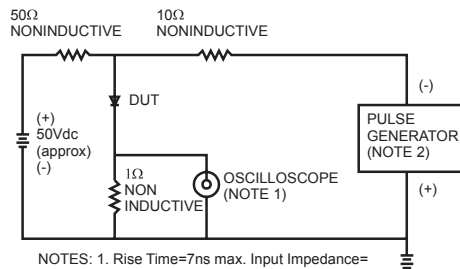


FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM



- NOTES: 1. Rise Time=7ns max. Input Impedance= 1 megohm 22pf
2. Rise Time=10ns max. Source Impedance= 50 ohms

